



Design and Implementation of High Conversion Efficiency RF to DC Rectifier Based on Inverted Gate Topology of Class F GaN HEMT RF High Power Amplifier for Wireless Power Transfer

Final Project

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STATEMENT OF AUTHENTICITY OF FINAL PROJECT

I, the undersigned, certify that the contents of part or all of my Final Project entitled: "Design and Implementation of High Conversion Efficiency RF to DC Rectifier Based on Inverted Gate Topology of Class F GaN HEMT RF High Power Amplifier For Wireless Power Transfer" is my own work, completed without the use of materials that are not permitted, and is not the work of other parties which I acknowledge as my own work. All references cited or referred to have been written in full in the bibliography. If it turns out that my statement is not true, I am willing to accept sanctions in accordance with applicable regulations.

Batam, 24th July 2026



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**The Final Project is structured to fulfill one of the requirements for
of Associate Engineer (A.Md.T
in
Batam State Polytechnic
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Session date: 24 July, 2026
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